

Manufacturer: inchange semiconductor company limited. request stock & quotation: ecad model: datasheets: ygw60n65f1. type designator: ygw60n65t1. uninterrupted power supply. designed for : frequency converters.

maximum junction temperature 175° c. short circuit withstand time 5 s. ygw60n65f1a1 650v / 60a trench field stop igbt lu- semi 650v trench field stop igbts offer v 650 v celow switching losses, high energy efficiency i 60 a cand high avalanche ruggedness for motion control, solar application and welding machine. datasheet - lcsc electronics.

, - pdf catalogs | technical documentation | brochure. com/ lcsc/ _ luxin- semi- ygw60n65f1a2_ c4153740.) maximum junction temperature 175° c. rongtech 650v trench field stop igbts offer low switching losses, high energy efficiency and high avalanche ruggedness for motion control, solar application and welding machine. ygw60n65f1; part number: ygw60n65f1: manufacturer: lx: description: lx + rohs: quantity available: 1444 pcs new original in stock. low saturation voltage: vce(sat) = 2. low gate charge qg. the devices are part of the new hb series of igbts which represent an optimum compromise between conduction and switching loss to maximize ygw60n65f1 pdf the efficiency of any frequency converter. high- frequency converters. this insulated gate bipolar transistor (igbt) features a robust and cost effective field stop (fs) trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. these are igbt devices developed using an advanced proprietary trench gate and field-stop structure.

ygw60n65f1a1 datasheet (pdf). maximum collector current | ic| a: 120. maximum gate- emitter voltage | vge|, v: 20. very fast soft recovery antiparallel diode. trenchstoptm and fieldstop technology for 600v applications offers: very tight parameter distribution. datasheet: 332kb/ 2p. maximum power dissipation (pc), w: 312. 75a 650v toigbts rohs. ygw40n65f1 transistor datasheet, ygw40n65f1 equivalent, pdf data sheets. high ruggedness, temperature stable behavior. features and benefits: high speed f5 technology offering.

these devices are igbts developed using an advanced proprietary trench gate field- stop structure. high current capability. extremely efficient trench. best- in- class efficiency in hard switching and resonant topologies.

converter with high switching frequency. ideal fit with sic schottky diode in boost converters. using novel field stop igbt technology, on semiconductor's new series of field stop 2nd generation igbts offer the optimum performance for solar inverter, ygw60n65f1 pdf ups, welder, telecom, ess and pfc applications where low conduction and switching losses are essential. igbt ngtb75n65fl2wg.

maximum collector- emitter voltage | vce|, v: 650. very low vce(sat) 1. part # : fcb260n65s3. electronic component catalog. photovoltaic inverters. pdf: ygw60n65f1 price: request price & lead time online or email us: com.

high speed switching high ruggedness. furthermore, a slightly positive vce(sat. description: insulated-gate bipolar transistor in a to- 3p plastic package. parameters and characteristics. sharing is caring,

show love and share the product with your friends. catalog excerpts. maximum junction temperature: $tj = 175^{\circ} c$.

ygw75n65f1 transistor datasheet, ygw75n65f1 equivalent, pdf data sheets. using novel field stop igbt technology, on semiconductor's field stop igbts offer the optimum performance for solar inverter, ups, welder and pfc applications where low conduction and switching losses are essential. 650v breakdown voltage. ygw60n65f1 null, ygw60n65f1 datasheet free, ygw60n65f1 pdf, ygw60n65f1 buy price, ygw60n65f1 description, ygw60n65f1 sellers, ygw60n65f1 semiconductors, electronic components. with field stop technology. collector- emitter saturation voltage | vce (sat) |, typ, v: 1. type of igbt channel: n. rgw60n65f1a 650v / 60a trench field stop igbt - rongtech industry (shanghai) inc. electronic components datasheet search 3 v @ ic = 60 a high input impedance. ygw40n65f1■■■■pdf■■. type designator: ygw60n65f1a2.